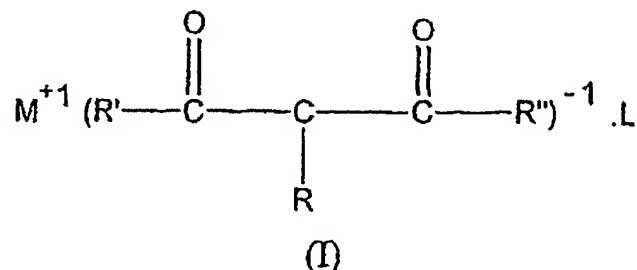


Amendments to the Claims:

1. (Original) A compound, characterized in that it corresponds to formula (I) below:

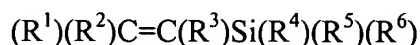


in which

- M represents a copper atom or silver atom;
- R' and R'', which may be identical or different, represent a group chosen from: a C₁-C₈ alkyl; an -OR''' group, in which R''' represents a C₁-C₈ alkyl;
- R represents a group chosen from: an -OR'''' group, in which R'''' represents a C₁-C₈ alkyl; a nitro group: NO₂; an aldehyde function: -CHO; a -COOR'''' ester function, in which R'''' represents a C₁-C₈ alkyl group;
- L represents a stabilizing ligand.

2. (Original) A compound according to formula (I), characterized in that L is chosen from:

- a- carbon monoxide,
- b- unsaturated hydrocarbon-based ligands containing at least one nonaromatic unsaturation,
- c- isonitriles,
- d- phosphines,
- e- the compounds corresponding to formula (II) below:



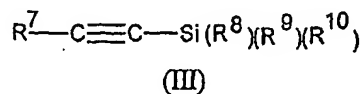
in which

- R¹ represents the hydrogen atom or a C₁-C₈ alkyl group or an SiR⁴R⁵R⁶ group,

- R^2 and R^3 , which may be identical or different, represent the hydrogen atom or a C_1 - C_8 alkyl group,

- R^4 , R^5 and R^6 , which may be identical or different, represent a phenyl or C_1 - C_8 alkyl group;

f- the compounds corresponding to formula (III) below:

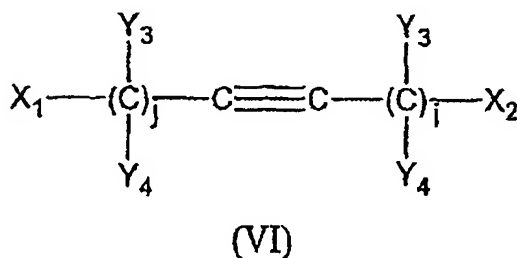
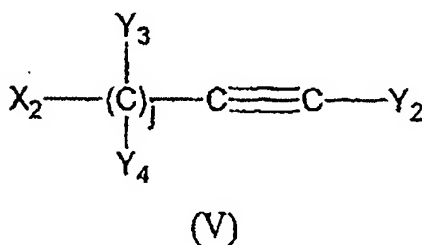
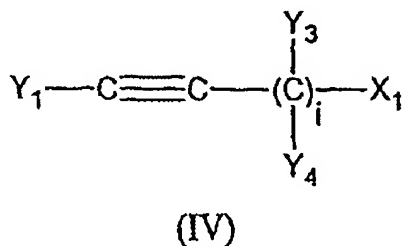


in which

- R^7 represents a C_1 - C_8 alkyl, phenyl or $Si(R^8)(R^9)(R^{10})$ group,

- R^8 , R^9 and R^{10} , which may be identical or different, represent a C_1 - C_8 alkyl or phenyl group,

g- the compounds corresponding to one of the formulae (IV), (V) and (VI) below:



in which Y_1 , Y_2 , Y_3 and Y_4 , which may be identical or different, are chosen from a hydrogen atom, a C_1 - C_8 alkyl and an $-Si(R_5)_3$ group where R_5 is a C_1 - C_8 alkyl, i and j represent an integer chosen from 0, 1, 2 and 3, and X_1 and X_2 , which may be identical or different, represent an electron-withdrawing group, such as in particular a C_1 - C_8 alkenyl.

3. (Currently Amended) A compound as claimed in claim 1, ~~wherein or claim 2,~~
~~characterized in that~~ M represents the copper atom.

4. (Currently Amended) A compound as claimed in claim 1, ~~wherein any one of~~
~~claims 1 to 3, characterized in that~~ R' or R'' represents a group chosen from CH_3 and C_2H_5 .

5. (Currently Amended) A compound as claimed claim 1, ~~wherein in any one of~~
~~claims 1 to 4, characterized in that~~ R represents a group chosen from NO_2 and OCH_3 .

6. (Currently Amended) A compound as claimed in claim 1, ~~wherein any one of~~
~~claims 1 to 5, characterized in that~~ L represents a ligand chosen from 1,5-cyclooctadiene and bis(trimethylsilyl)acetylene.

7. (Currently Amended) A process for the gas-phase chemical deposition of a metal chosen from copper and silver, on a support, this process being characterized in that a compound as claimed in claim 1 ~~any one of claims 1 to 6~~ is used as a copper precursor or silver precursor.

8. (Currently Amended) The process as claimed in claim 7, ~~wherein characterized~~
~~in that~~ the support consists of a material chosen from Si, AsGa, InP, SiC and SiGe.

9. (Currently Amended) The process as claimed in claim 7, ~~wherein either one of~~
~~claims 7 and 8, characterized in that~~ the support contains one or more intermediate layers consisting of at least one material chosen from TiN, TiSiN, Ta, TaN, TaSiN, WN and WSiN.

10. (Currently Amended) The process as claimed in claim 7, wherein ~~any one of claims 7 to 9, characterized in that~~ it is carried out at a temperature ranging from 120 to 300°C.

11. (Currently Amended) The process as claimed in claim 7, wherein ~~any one of claims 7 to 10, characterized in that~~ the copper precursor or silver precursor is used pure.

12. (Currently Amended) The process as claimed in claim 7, wherein ~~any one of claims 7 to 10, characterized in that~~ the copper precursor or silver precursor is used in solution in a solvent.

13. (Currently Amended) The use of a process as claimed in claim 7 ~~any one of claims 7 to 12,~~ for depositing a layer of copper or of silver having a thickness ranging from 0.2 to 500 nm.

14. (Currently Amended) The use of a process as claimed in claim 7 ~~any one of claims 7 to 12,~~ for producing an integrated circuit.